Vishay Siliconix



SOT-23 (TO-236)

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.170			
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.230			
I _D (A)	-2.9			
Configuration	Single			

P-Channel MOSFET

FEATURES

- TrenchFET® power MOSFET
- Typical ESD protection: 800 V
- AEC-Q101 qualified
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





Marking Code: 9Cxxx

D

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2361AEES-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current	T _C = 25 °C		-2.8		
	T _C = 125 °C	l _D	-1.6		
Continuous Source Current (Diode Conduction)		I _S	-2.5	А	
Pulsed Drain Current ^a		I _{DM}	-11		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-13		
Single Pulse Avalanche Energy	L=0.11III	E _{AS}	8.4	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	2	W	
	T _C = 125 °C		0.67	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount b	R_{thJA}	175	°C/W
Junction-to-Foot (Drain)		R_{thJF}	75	C/ VV

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-	-2.5	V	
Gate-Source Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 30	mA	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	± 2		
		$V_{GS} = 0 V$	V _{DS} = -60 V	ı	-	-1] ,,,	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	- μΑ	
		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	-	-	-150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-10	-	=	Α	
		V _{GS} = -10 V	I _D = -2.4 A	-	0.130	0.170		
Drain-Source On-State Resistance a	В	V _{GS} = -10 V	I _D = -2.4 A, T _J = 125 °C	-	-	0.300	Ω	
Drain-Source On-State nesistance *	R _{DS(on)}	V _{GS} = -10 V	I _D = -2.4 A, T _J = 175 °C	-	-	0.315		
		$V_{GS} = -4.5 \text{ V}$	I _D = -1.8 A	-	0.180	0.230		
Forward Transconductance b	9 _{fs}	V _{DS}	= -10 V, I _D = -2 A	-	5	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	415	620		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -30 V, f = 1 MHz		55	80	pF	
Reverse Transfer Capacitance	C _{rss}			-	32	45		
Total Gate Charge c	Q_g			-	10	15		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = -10 V	$V_{DS} = -30 \text{ V}, I_{D} = -6 \text{ A}$	-	1.5	-	nC	
Gate-Drain Charge ^c	Q_{gd}	1 [ı	5	-		
Gate Resistance	R_g	f = 1 MHz		3.2	4.3	5.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	9	12		
Rise Time ^c	t _r	V_{DD} = -30 V, R_L = 20 Ω $I_D \cong$ -1.5 A, V_{GEN} = -10 V, R_g = 1 Ω		ı	9	12	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			ı	24	30		
Fall Time ^c	t _f			-	4	6		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I _{SM}			-	-	-13	Α	
Forward Voltage	V_{SD}	I _F = -1.5 A, V _{GS} = 0 V		-	-0.8	-1.2	٧	

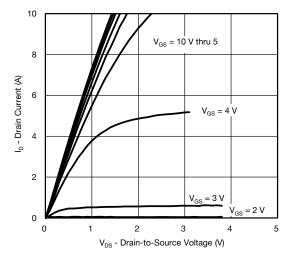
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

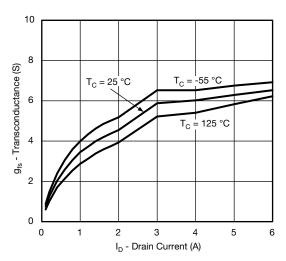
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



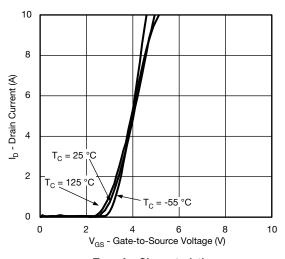
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



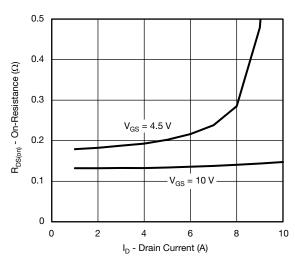
Output Characteristics



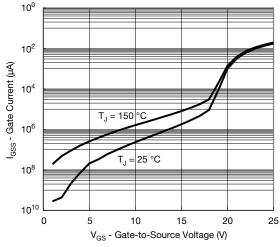
Transconductance



Transfer Characteristics



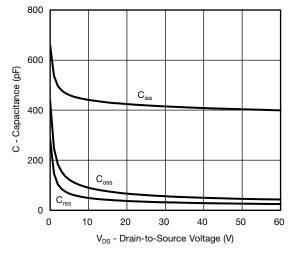
On-Resistance vs. Drain Current



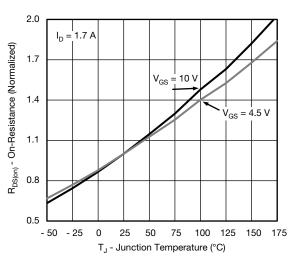
Gate Current vs. Gate-Source Voltage



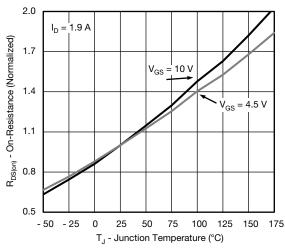
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



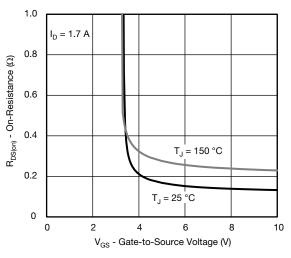
Capacitance



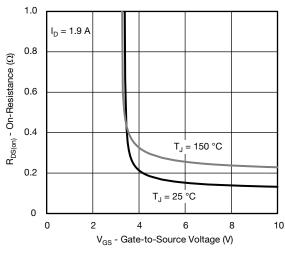
On-Resistance vs. Junction Temperature



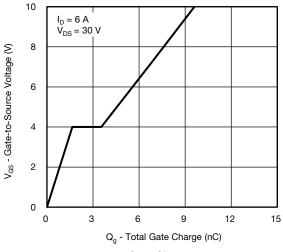
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-Source Voltage



On-Resistance vs. Gate-Source Voltage

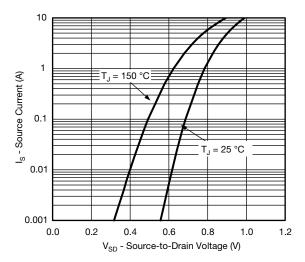


Gate Charge

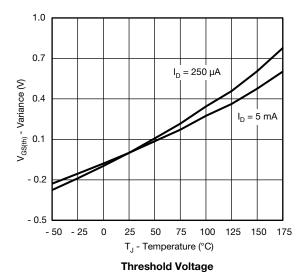
For technical questions, contact: automostech



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

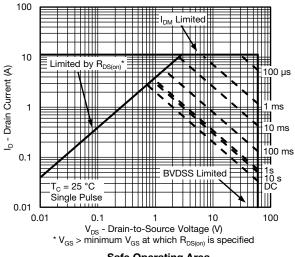


Source-Drain Diode Forward Voltage



- 55 $I_D = 1 \text{ mA}$ V_{DS} - Drain-to-Source Voltage (V) - 59 - 63 - 67 - 75 - 50 - 25 25 50 75 100 125 150 0 T_J - Junction Temperature (°C)

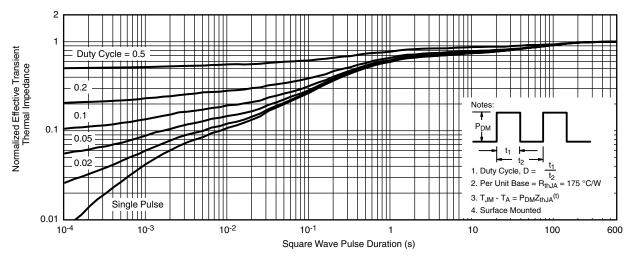
Drain Source Breakdown vs. Junction Temperature



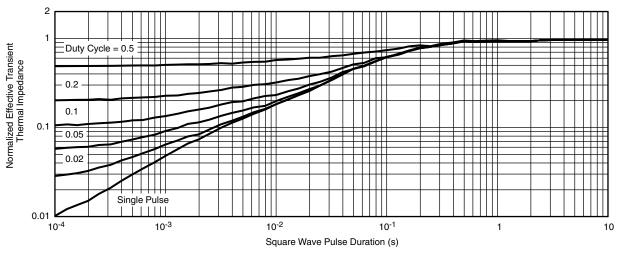
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

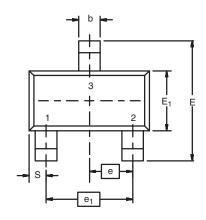
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

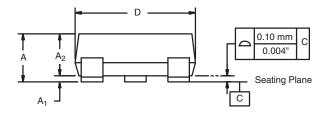
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

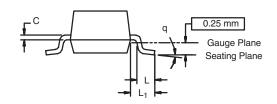
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SOT-23 (TO-236): 3-LEAD







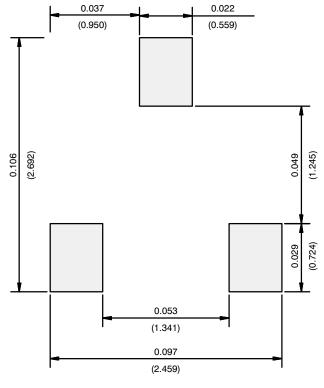
Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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